L Number	Hits	Search Text	DB	Time stamp
15	7	(boe or buffer$3 near2 oxid$2 near2 etch$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric) same combination	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/28 10:25
16	90	(boe or buffer$3 near2 oxid$2 near2 etch$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/28 10:26
17	20	(boe or buffer$3 near2 oxid$2 near2 etch$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric) same (HF)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/28 10:32
–	118	(contact near5 plug same (silicon or si) and temperature near3 (deposit$4 or grow$4) near10 (silicon or si)) and (lpcvd or low near2 pressure near2 chemical near2 vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:19
–	14	contact near5 plug same (silicon or si) and temperature near3 (deposit$4 or grow$4) near10 (silicon or si) same epitax$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:37
–	84	selectiv$4 near3 epitax$4 near10 (silicon or si or polysilicon) and (low near2 pressure near3 chemical near2 vapor or lpcvd) and two near10 (deposit$4 or grow$4 or epitax$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:51
–	38	((silicon or si) near4 amorphous or polysilicon) same plug near5 contact same (low near4 pressure or lpcvd) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 17:00
–	24	((silicon or si) near4 amorphous or polysilicon) near10 plug near5 contact same (low near4 pressure or lpcvd) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 17:00
–	81	contact near5 plug same (single or epitax$4) near5 (si or silicon) same (amorphous near4 (silicon) or poly or poly$1si or poly$1silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 14:59
–	40	(contact near5 plug same (single or epitax$4) near5 (si or silicon) same (amorphous near4 (silicon) or poly or poly$1si or poly$1silicon)) and (lpcvd or low near3 pressure near3 chemical near2 vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 15:18
–	10	(lpcvd or low near3 pressure near3 chemical near2 vapor) and selective near4 (epitax$4 or grow$4 or deposit$4) same contact near4 plug same (single or epitax$4) near5 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 15:51
–	53	(lpcvd or low near3 pressure near3 chemical near2 vapor) and contact near4 plug near10 (silicon or si) and flow near3 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 15:55
–	18	(lpcvd or low near3 pressure near3 chemical near2 vapor) and contact near4 plug near10 (silicon or si) and flow near3 rate same temperature same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 15:56

–	58	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) same plug same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 16:24
–	3	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) near10 (crystal$4 or crystallin$4) same plug same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 16:26
–	62	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) near10 (crystal$4 or crystallin$4) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 16:26
–	6	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) near10 (crystal$4 or crystallin$4) near10 select$5 same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 16:31
–	28	(lpcvd or low near2 pressure near2 chemical) same (silicon or si) near10 (crystal$4 or crystallin$4) near10 select$5 same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 16:35
–	84	(lpcvd or low near2 pressure near2 chemical) and (silicon or si) near10 (crystal$4 or crystallin$4) near10 select$5 near4 (epitax$4 or grow$4 or deposit$4) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 16:57
–	56	(NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same clean$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 10:22
–	5	(NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same clean$4 same (contact or plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 11:10
–	4	clean$4 same (contact or plug) same (boe or buffer$3 near2 oxid$2 near2 etch$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 09:43
–	30	clean$4 same (boe or buffer$3 near2 oxid$2 near2 etch$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/28 10:18
–	0	wet near4 etch$4 same (dry or plasma) near3 etch$4 same clean$4 same (contact or plug or via) same (NF3 or "nf.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 09:49
–	9	wet near4 etch$4 same (dry or plasma) near3 etch$4 same clean$4 same (contact or plug or via) same bak$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 09:50
–	25	((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma) and (boe or buffer$3 near2 oxid$3 near3 etch$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 09:53
–	128	(boe or buffer$3 near2 oxid$3 near3 etch$4) same (h2so4 or "h.sub.2so.sub.4" or sulfur$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 09:59

–	18	((boe or buffer$3 near2 oxid$3 near3 etch$4) same (h2so4 or "h.sub.2so.sub.4" or sulfur$3)) same (contact or via or plug or trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 09:57
–	34	(boe or buffer$3 near2 oxid$3 near3 etch$4) same (h2so4 or "h.sub.2so.sub.4" or sulfur$3) same clean$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 10:00
–	39	(NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 same (via or hole or contact or plug or trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 10:52
–	95	((NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 and (via or hole or contact or plug or trench)) not ((NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 same (via or hole or contact or plug or trench)) not (((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma) and (boe or buffer$3 near2 oxid$3 near3 etch$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 10:54
–	71	((NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 and (via or hole or contact or plug or trench)) not ((NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 same (via or hole or contact or plug or trench)) not (((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma) and (boe or buffer$3 near2 oxid$3 near3 etch$4)) not ((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same clean$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 10:54
–	71	((NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 and (via or hole or contact or plug or trench)) not ((NF3 or "NF.sub.3" or fluor$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean$4 same (via or hole or contact or plug or trench)) not (((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma) and (boe or buffer$3 near2 oxid$3 near3 etch$4)) not ((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same clean$4) not (clean$4 same (boe or buffer$3 near2 oxid$2 near2 etch$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 10:56
–	51	(wet same (dry or plasma) same clean$4 same etch$4 same (via or hole or contact or plug or residu$4)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 11:02
–	113	((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same etch$4) not ((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same clean$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/06 11:34
–	38	(NF3 or "Nf.sub.3" or fluor$4) near20 (o2 or "o.sub.2" or oxygen) near5 plasma same (clean$4) same (via or contact or hole or trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 15:27

-		68	(NF3 or "Nf.sub.3") near20 (o2 or "o.sub.2" or oxygen) near5 plasma same (clean$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 15:44
-		55	dry near10 wet same bak$4 same clean$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:32
-		22	(sulfuric or "H.sub.2So.sub.4" or h2so4) near10 (boe or buffer$3 near2 oxide near2 etch$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:15
-		22	(sulfuric or "H.sub.2So.sub.4" or h2so4) near10 (boe or buffer$3 near2 oxid$3 near2 etch$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:27
-		94	(sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer$3 near2 oxid$3 near2 etch$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:28
-		30	(sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer$3 near2 oxid$3 near2 etch$4) same clean$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:32
-		8	(sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer$3 near2 oxid$3 near2 etch$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:33
-		23	clean$4 same (wet or acid) same (dry or plasma) same (bak$4) same semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/09 18:53
-		50	wet near10 clean$4 same plug same dry	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 17:49
-		33	wet near10 clean$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) and dry near10 clean$4 and bak$4 and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 17:58
-		1	shin.in. and contact same clean$4 and wet and dry and bak$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:02
-		1	shin.in. and contact same clean$4 same "H.sub.2so.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:03
-		9	shin.in. and contact same clean$4 same wet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:11
-		27	((("nf.sub.3" or nf3) or Nitrogen near2 trifluoride) near30 clean$4) same (contact or via or trench$4) same plasma same (oxygen or o2 or "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:29

–	2	2000100749.pn.		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:34
–	85	(contact or via or trench) near20 clean$4 same (combinat$4 or combin$4) near10 (dry or plasma)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:41
–	40	(contact or via or trench) near20 clean$4 same (combinat$4) near10 (dry or plasma)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 18:43
–	37	(silicon or si) near4 (single or epitax$4) same plug same (lpcvd or low near4 pressur$4)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 16:53
–	28	(silicon or si) near4 (single or epitax$4) near20 selectiv$5 same (lpcvd or low near4 pressur$4) near10 temperature		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 17:07
–	14	(silicon or si) near4 (single or epitax$4) near20 selectiv$5 same (lpcvd or low near4 pressur$4) near20 torr		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:39
–	15	(silicon or si) near4 (single or epitax$4) same (lpcvd) near20 torr		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:42
–	9	(lpcvd).ti. and silicon near5 (epitax$4 or grow$4 or deposit$4) same torr		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:01
–	15	(seg or selective near2 epitax$4) near15 (si or silicon) same (contact or plug or via) and (h2 or "h.sub.2" or hydrogen) near5 bak$4		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:11
–	8	combinat$4 near10 wet near10 dry near10 bak$4		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:12
–	9	((bak$4 or anneal$4 or rapid near3 thermal or heat near2 treat$4 or rta or rtp or ptp) near25 (hydrogen or h2 or "h.sub.2")) near30 combinat$4 near20 clean$4		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:17
–	5	((bak$4 or anneal$4 or rapid near3 thermal or heat near2 treat$4 or rta or rtp or ptp) near25 (hydrogen or h2 or "h.sub.2")) near30 combinat$4 same (contact or plug)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:18
–	41	((bak$4 or anneal$4 or rapid near3 thermal or heat near2 treat$4 or rta or rtp or ptp) near25 (hydrogen or h2 or "h.sub.2")) near30 (contact or plug) same plasma		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:19
–	2	6111277.pn.		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 13:01

–	17	(silicon or si) near10 (select$4 or selectiv$4) near5 (epitax$4 or grow$4 or deposit$4) near30 (cone or conical or pyramid$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 13:17
–	93	(silicon or si) near10 (select$4 or selectiv$4) near30 (cone or conical or pyramid$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 13:15
–	76	((silicon or si) near10 (select$4 or selectiv$4) near30 (cone or conical or pyramid$4)) not ((silicon or si) near10 (select$4 or selectiv$4) near5 (epitax$4 or grow$4 or deposit$4) near30 (cone or conical or pyramid$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 13:15
–	8	(silicon or si) near10 (select$4 or selectiv$4) near5 (epitax$4 or grow$4 or deposit$4) near30 (peak)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:10
–	105	carrier near5 gas$4 near20 smooth	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:25
–	10	(carrier near5 gas$4 near20 smooth) same CVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:24
–	7	(carrier near5 gas$4 near20 smooth) same chemical near3 vapor near2 deposit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:24
–	17	carrier near5 gas$4 near20 smooth near4 flow and CVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:27
–	68	CVD same Process near5 parameter near10 flow near4 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:33
–	13	LPCVD same Process near5 parameter near10 flow near4 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 17:35
–	34	LPCVD same parameter near10 flow near4 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 18:31
–	10	((h2so4 or "h.sub.2.so.sub.4" or sulfuric) near20 clean$4) same (buffer$4 near2 oxide or boe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 18:55